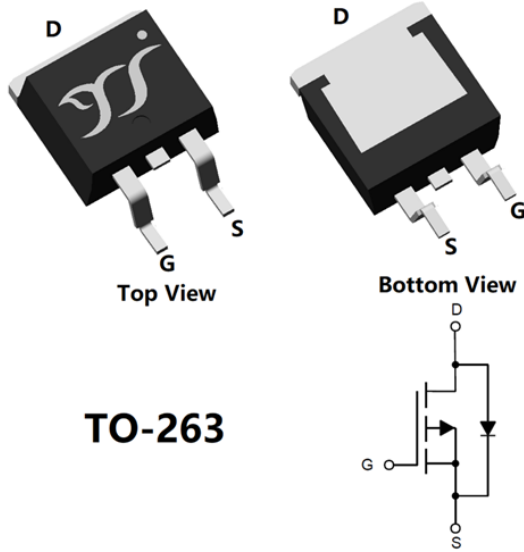


P-Channel Enhancement Mode Field Effect Transistor



Product Summary

• V_{DS}	-100V
• I_D	-30A
• $R_{DS(ON)}$ (at $V_{GS}=-10V$)	<56 mohm
• $R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	<62 mohm
• 100% EAS Tested	
• 100% ∇V_{DS} Tested	
• ESD Level (HBM)	H1C

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- DC-DC Converters
- Power management functions

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_C=25^\circ\text{C}$	I_D	-30	A
	$T_C=100^\circ\text{C}$		-19.2	
Pulsed Drain Current ^A		I_{DM}	-120	A
Avalanche energy ^B		E_{AS}	162	mJ
Total Power Dissipation ^C	$T_C=25^\circ\text{C}$	P_D	125	W
	$T_C=100^\circ\text{C}$		50	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	$t \leq 10S$	$R_{\theta JA}$	12	15	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Ambient ^D	Steady-State		50	60	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.8	1.0	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB30GP10A	F2	YJB30GP10A	800	/	8000	13" reel



YJB30GP10A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions		Min	Typ	Max	Units
Static Parameter							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA		-100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V	T _J =25℃			-1	μA
			T _J =55℃			-5	
			T _J =125℃			-10	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V				±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA		-1.0	-1.8	-2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D =-15A			42	56	mΩ
		V _{GS} = -4.5V, I _D =-7A			46	62	
Diode Forward Voltage	V _{SD}	I _S =-15A, V _{GS} =0V				-1.3	V
Maximum Body-Diode Continuous Current	I _S					-30	A
Dynamic Parameters							
Input Capacitance	C _{iSS}	V _{DS} =-50V, V _{GS} =0V, f=1MHZ			2100		pF
Output Capacitance	C _{oSS}				236		
Reverse Transfer Capacitance	C _{rSS}				48		
Switching Parameters							
Total Gate Charge	Q _g (-10V)	V _{GS} =-10V, V _{DS} =-50V, I _D =-5A			40		nC
Total Gate Charge	Q _g (-4.5V)				19.4		
Gate-Source Charge	Q _{gs}				7.8		
Gate-Drain Charge	Q _{gd}				8.6		
Reverse Recovery Chrage	Q _{rr}	I _F =-5A, di/dt=100A/us			280		ns
Reverse Recovery Time	t _{rr}				104		
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-50V, I _{DS} =-5A R _{GEN} =6Ω			13		
Turn-on Rise Time	t _r				39		
Turn-off Delay Time	t _{D(off)}				100.1		
Turn-off fall Time	t _f				105.3		

A. Repetitive rating; pulse width limited by max. junction temperature.

B. V_{DD}=50V, R_G=25Ω, L=0.5mH.

C. Pd is based on max. junction temperature, using junction-case thermal resistance.

D. The value of RθJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation PDSM is based on RθJA ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.



■ Typical Performance Characteristics

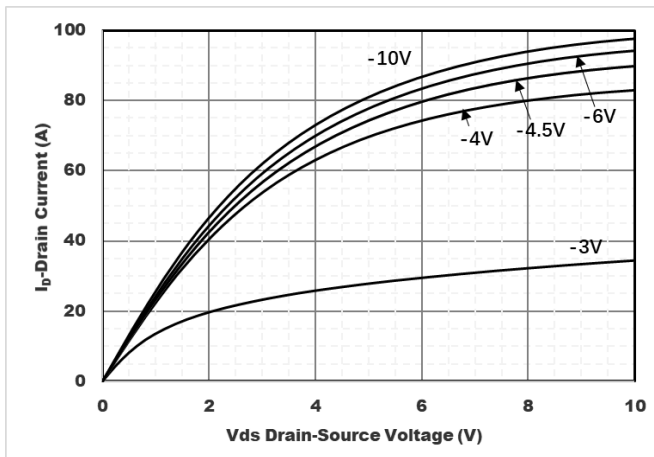


Figure1. Output Characteristics

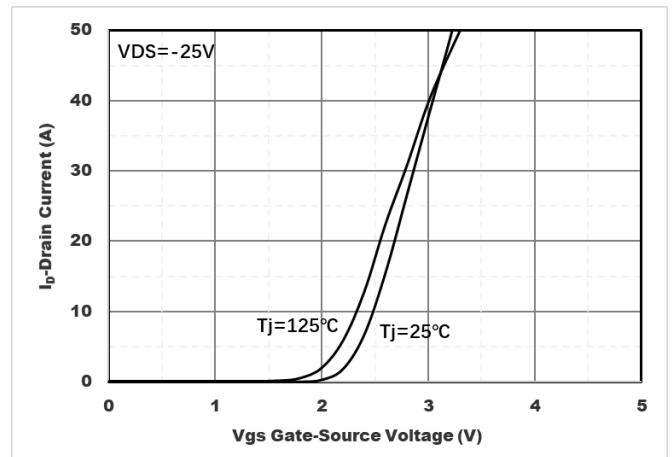


Figure2. Transfer Characteristics

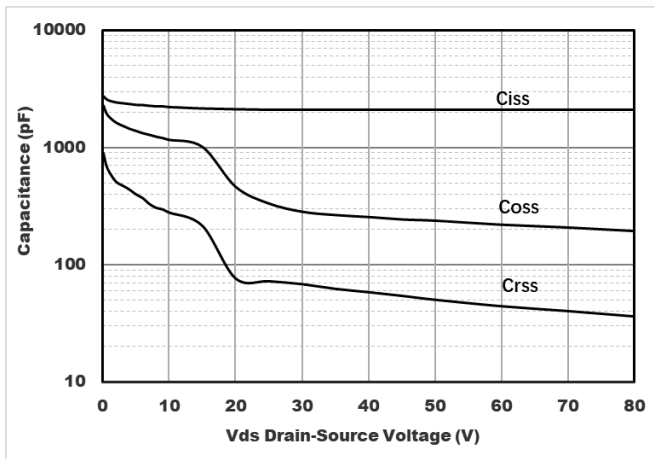


Figure3. Capacitance Characteristics

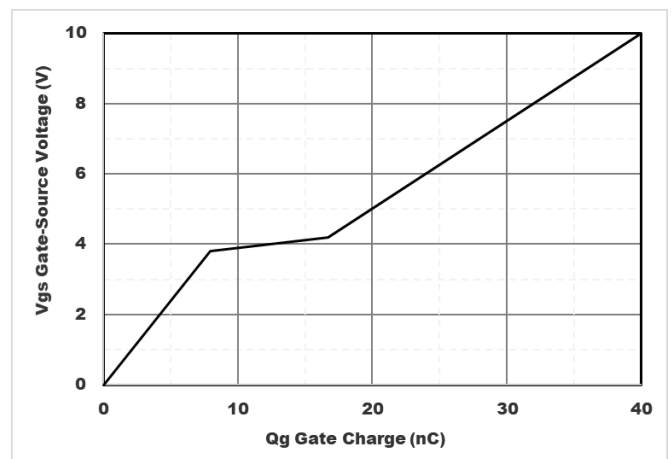


Figure4. Gate Charge

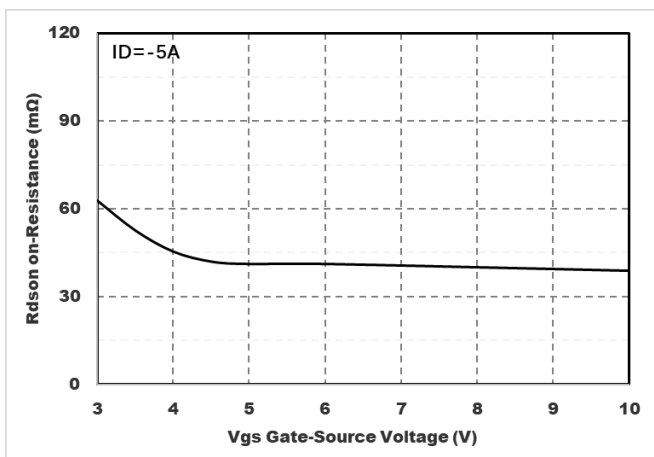


Figure5. : On-Resistance vs. Gate to Source Voltage

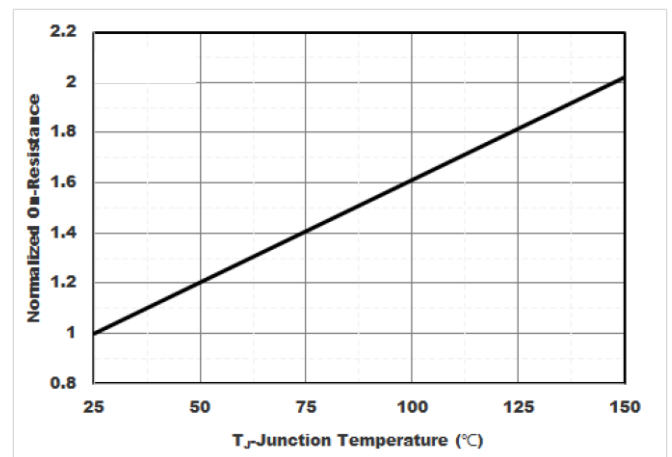


Figure6. Normalized On-Resistance



YJB30GP10A

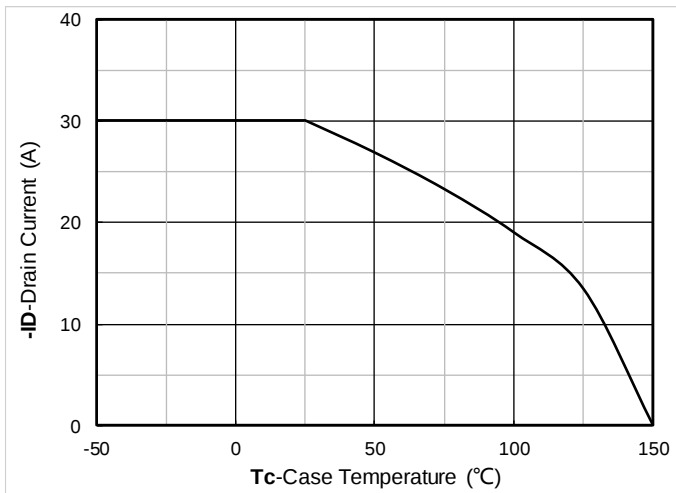


Figure7. Drain current

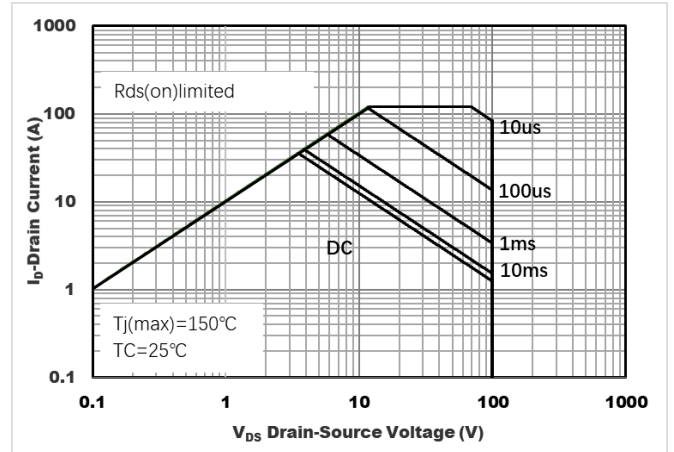


Figure8.Safe Operation Area

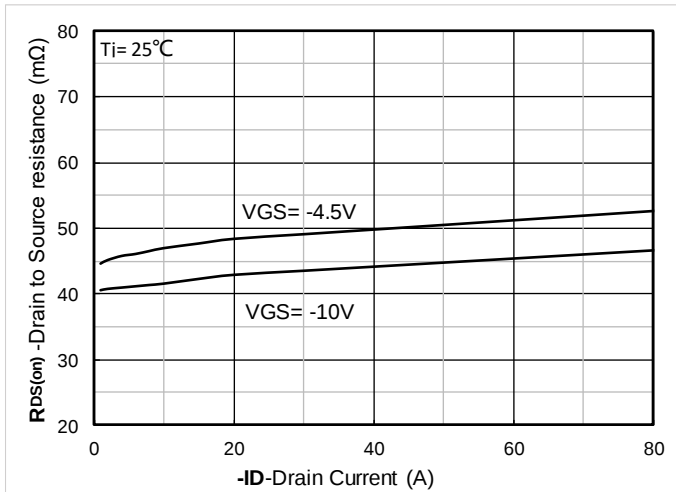


Figure9. RDS(on) VS Drain Current

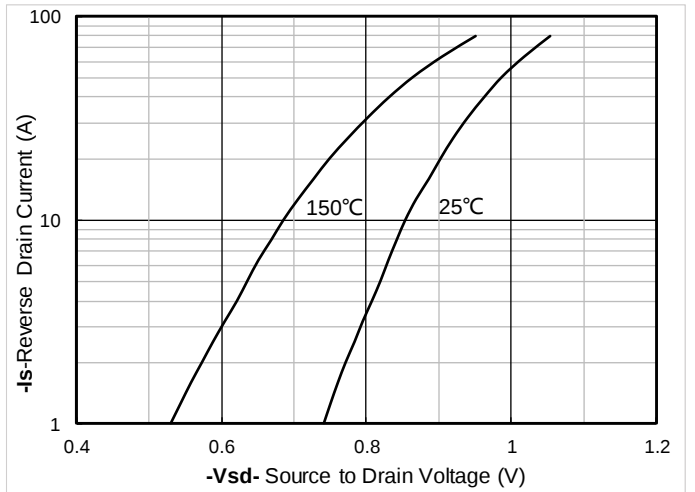


Figure 10. Forward characteristics of reverse diode

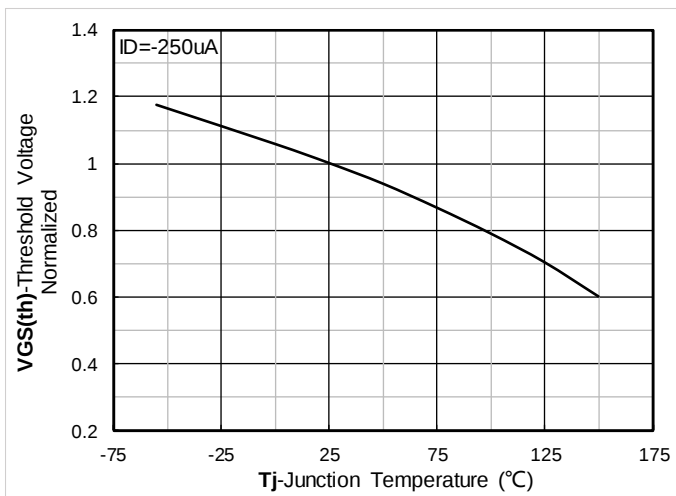


Figure 11. Normalized Threshold voltage

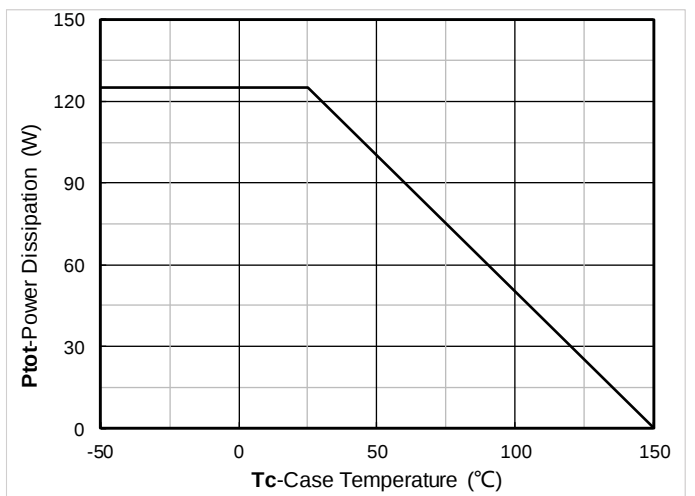
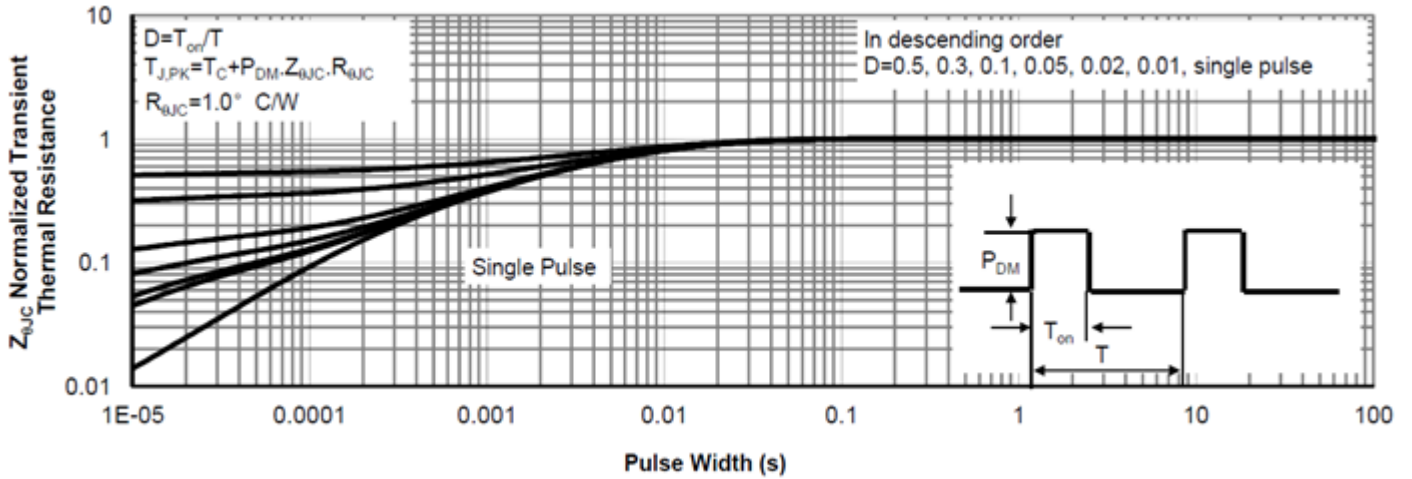
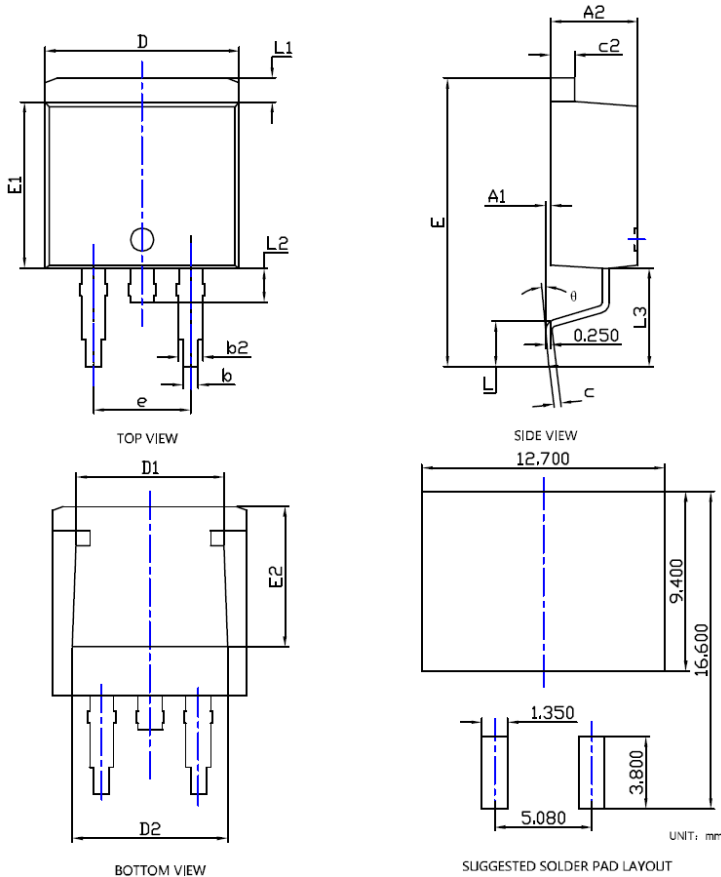


Figure 12. Power dissipation



TO-263 Package information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.280	1.34
D	0.394	0.400	0.406	10.000	10.150	10.300
D1	0.295	0.307	0.319	7.500	7.800	8.100
D2	0.303	0.315	0.327	7.700	8.000	8.300
E	0.571	0.591	0.610	14.500	15.000	15.500
E1	0.337	0.341	0.348	8.550	8.700	8.850
E2	0.276	0.287	0.299	7.000	7.300	7.600
e	0.200BSC			5.080BSC		
L	0.070	---	0.110	1.790	---	2.790
L1	0.044	---	0.056	1.120	---	1.420
L2	0.030	---	0.070	0.770	---	1.770
L3	0.197REF			5.000REF		
θ	0°	---	8°	0°	---	8°

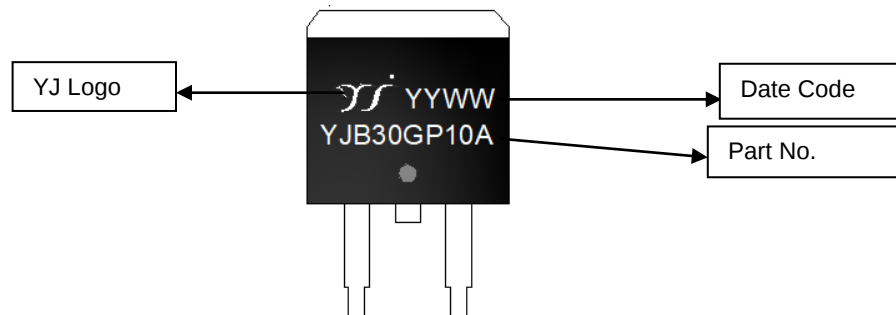
NOTE:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



YJB30GP10A

■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJB30GP10A is part no., YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



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